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DCX (xxxx) H

COMPLEMENTARY NPN/PNP PRE-BIASED SMALL SIGNAL DUAL SURFACE MOUNT TRANSISTOR

Features

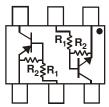
- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

P/N	R1	R2	MARKING
DCX124EH	22ΚΩ	22ΚΩ	C17
DCX144EH	47ΚΩ	47ΚΩ	C20
DCX143EH	4.7ΚΩ	4.7ΚΩ	C08
DCX114YH	10ΚΩ	47ΚΩ	C14
DCX123JH	2.2ΚΩ	47ΚΩ	C06
DCX114EH	10ΚΩ	10ΚΩ	C13
DCX143TH	4.7ΚΩ		C07
DCX114TH	10ΚΩ		C12

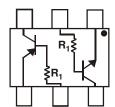
Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

SCHEMATIC DIAGRAM, TOP VIEW







R₁ Only Device Schematic

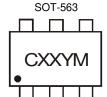
Ordering Information (Note 4)

Device	Packaging	Shipping
DCX124EH-7	SOT-563	3,000/Tape & Reel
DCX144EH-7	SOT-563	3,000/Tape & Reel
DCX143EH-7	SOT-563	3,000/Tape & Reel
DCX114YH-7	SOT-563	3,000/Tape & Reel
DCX123JH-7	SOT-563	3,000/Tape & Reel
DCX114EH-7	SOT-563	3,000/Tape & Reel
DCX143TH-7	SOT-563	3,000/Tape & Reel
DCX114TH-7	SOT-563	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



CXX = Product Type Marking Code YM = Date Code Marking Y = Year ex: P = 2003 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	Х	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings NPN Section (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		Vcc	50	V
Input Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH DCX143TH DCX114TH	Vin	-10 to +40 -10 to +40 -10 to +30 -6 to +40 -5 to +12 -10 to +40 -5V max -5V max	V
Output Current	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH DCX143TH DCX114TH	I _O	30 30 100 70 100 50 100 100	mA
Output Current	All	I _C (Max)	100	mA
Power Dissipation	(Total)	P _d	150	mW
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Note: 5. Mounted on FR4 Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.

Maximum Ratings PNP Section (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		Vcc	50	V
Input Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH DCX114TH	V _{IN}	+10 to -40 +10 to -40 +10 to -30 +6 to -40 +5 to -12 +10 to -40 +5V max +5V max	V
Output Current	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH DCX143TH DCX114TH	Io	-30 -30 -100 -70 -100 -50 -100	mA
Output Current	All	I _C (Max)	-100	mA
Power Dissipation (Total)		P _d	150	mW
Operating and Storage Temperature Range		Tj, T _{STG}	-55 to +150	°C



Electrical Characteristics NPN Section (@T_A = +25°C unless otherwise specified.)

Characteristic (DDC143TH	& DDC114TH only)	Symbol	Min	Тур	Ma	х	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	50		_		٧	$I_C = 50\mu A$
Collector-Emitter Breakdown Vo	Itage	BV _{CEO}	50		_		٧	I _C = 1mA
Emitter-Base Breakdown Voltag	е	BV _{EBO}	5	_		-	٧	$I_E = 50\mu A$
Collector Cut-Off Current		I _{CBO}			0.5	5	μΑ	$V_{CB} = 50V$
Emitter Cut-Off Current		I _{EBO}			0.5	5	μΑ	$V_{EB} = 4V$
Collector-Emitter Saturation Volt	age	V _{CE(sat)}	_	_	0.3	3	V	$I_C/I_B = 2.5 \text{mA} / 0.25 \text{mA}$ DCX143TH $I_C/I_B = 1 \text{mA} / 0.1 \text{mA}$ DCX114TH
DC Current Transfer Ratio		h _{FE}	100	250	600	0	_	$I_C = 1mA$, $V_{CE} = 5V$
Gain-Bandwidth Product*		f _T	_	250	_	.	ИНz	V _{CE} = 10V, I _E = -5mA, f = 100MHz
Characteris	stic	Symbol	Mir	1	Тур	Max	Unit	Test Condition
	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{I(off)}	0.5 0.5 0.5 0.3 0.5	; ; ;	1.1 1.1 1.1 — — 1.1	_	V	$V_{CC} = 5V$, $I_{O} = 100 \mu A$
Input Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{I(on)}	_		1.9 1.9 1.9 — — 1.9	3.0 3.0 3.0 1.4 1.1 3.0	_	$V_O = 0.3V$, $I_O = 5mA$ $V_O = 0.3V$, $I_O = 2mA$ $V_O = 0.3V$, $I_O = 20mA$ $V_O = 0.3V$, $I_O = 1mA$ $V_O = 0.3V$, $I_O = 5mA$ $V_O = 0.3V$, $I_O = 10mA$
Output Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{O(on)}	_		0.1	0.3	V	I _O /I _I = 10mA / 0.5mA I _O /I _I = 10mA / 0.5mA I _O /I _I = 10mA / 0.5mA I _O /I _I = 5mA / 0.25mA I _O /I _I = 5mA / 0.25mA I _O /I _I = 10mA / 0.5mA
Input Current	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	lı	_		_	0.36 0.18 1.8 0.88 3.6 0.88	mA	V _I = 5V
Output Current		I _{O(off)}	_			0.5	μΑ	$V_{CC} = 50V$, $V_I = 0V$
DC Current Gain	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	G _l	56 68 20 68 80 30			_	_	$V_{O} = 5V, I_{O} = 5mA$ $V_{O} = 5V, I_{O} = 5mA$ $V_{O} = 5V, I_{O} = 10mA$ $V_{O} = 5V, I_{O} = 10mA$ $V_{O} = 5V, I_{O} = 10mA$ $V_{O} = 5V, I_{O} = 5mA$

^{*} Transistor - For Reference Only



Electrical Characteristics PNP Section (@T_A = +25°C unless otherwise specified.)

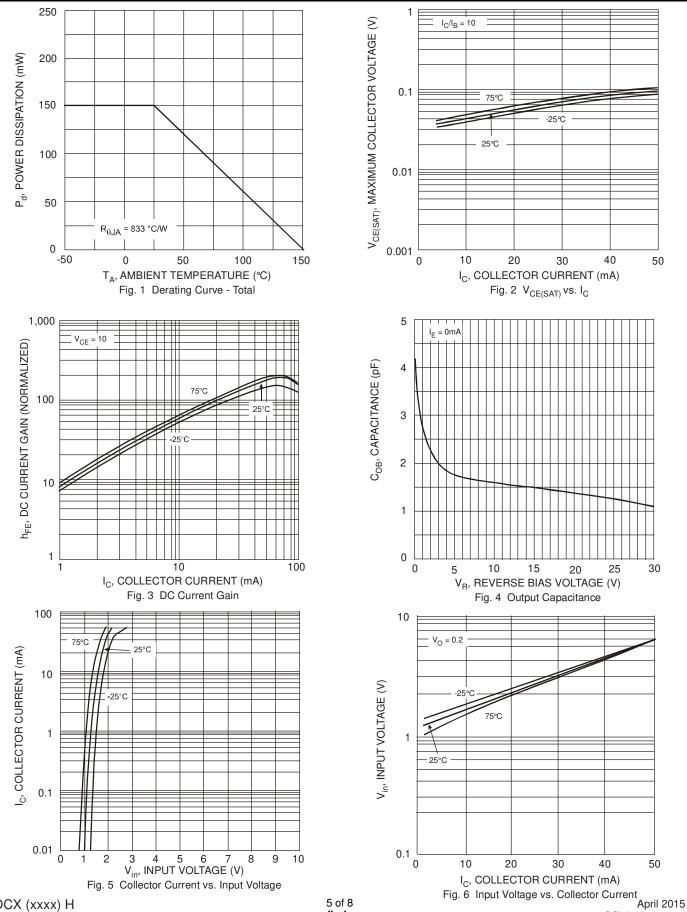
Characteristic (DCX143TH & DCX114TH only)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_	_	٧	$I_C = -50\mu A$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50	_	_	٧	I _C = -1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	_	٧	I _E = -50μA
Collector Cut-Off Current	I _{CBO}	_	_	-0.5	μΑ	V _{CB} = -50V
Emitter Cut-Off Current	I _{EBO}	_	_	-0.5	μΑ	V _{EB} = -4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		_	-0.3	V	$I_C/I_B = 2.5 \text{mA} / 0.25 \text{mA}$ DCX143TH $I_C/I_B = 1 \text{mA} / 0.1 \text{mA}$ DCX114TH
DC Current Transfer Ratio	h _{FE}	100	250	600		$I_C = -1mA$, $V_{CE} = -5V$
Gain-Bandwidth Product*	f⊤	_	250	_	MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz

Characteri	Characteristic		Min	Тур	Max	Unit	Test Condition
	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{I(off)}	-0.5 -0.5 -0.5 -0.3 -0.5 -0.5	-1.1 -1.1 -1.1 — — —	_		$V_{CC} = -5V$, $I_{O} = -100 \mu A$
Input Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{I(on)}		-1.9 -1.9 -1.9 — — -1.9	-3.0 -3.0 -3.0 -1.4 -1.1 -3.0	V	$\begin{split} &V_O = -0.3V, \ I_O = -5mA \\ &V_O = -0.3V, \ I_O = -2mA \\ &V_O = -0.3V, \ I_O = -20mA \\ &V_O = -0.3V, \ I_O = -1mA \\ &V_O = -0.3V, \ I_O = -5mA \\ &V_O = -0.3V, \ I_O = -10mA \end{split}$
Output Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{O(on)}		-0.1	-0.3	V	$\begin{split} &I_O/I_I = -10\text{mA} \ / \ -0.5\text{mA} \\ &I_O/I_I = -10\text{mA} \ / \ -0.5\text{mA} \\ &I_O/I_I = -10\text{mA} \ / \ -0.5\text{mA} \\ &I_O/I_I = -5\text{mA} \ / \ -0.25\text{mA} \\ &I_O/I_I = -5\text{mA} \ / \ -0.25\text{mA} \\ &I_O/I_I = -10\text{mA} \ / \ -0.5\text{mA} \end{split}$
Input Current	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	lı	_	_	-0.36 -0.18 -1.8 -0.88 -3.6 -0.88	mA	V ₁ = -5V
Output Current		I _{O(off)}	_	_	-0.5	μΑ	$V_{CC} = 50V$, $V_I = 0V$
DC Current Gain	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	Gı	56 68 20 68 80 30	_	_	_	$V_O = -5V$, $I_O = -5mA$ $V_O = -5V$, $I_O = -5mA$ $V_O = -5V$, $I_O = -10mA$ $V_O = -5V$, $I_O = -10mA$ $V_O = -5V$, $I_O = -10mA$ $V_O = -5V$, $I_O = -5mA$
Gain-Bandwidth Product*	'	f⊤	_	250	_	MHz	

^{*} Transistor - For Reference Only

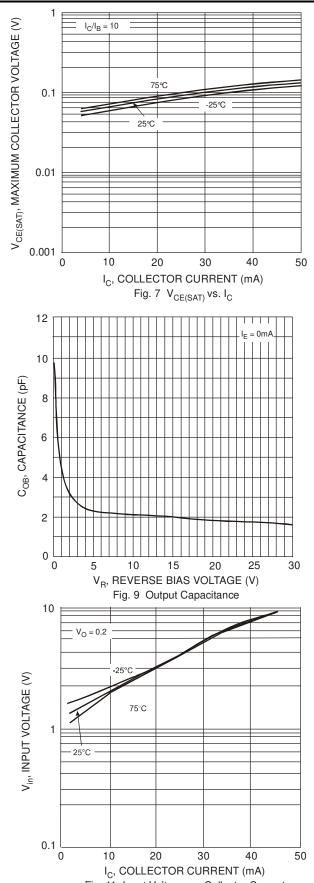


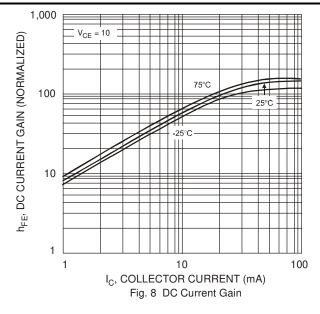
Typical Curves - DCX143EH NPN Section

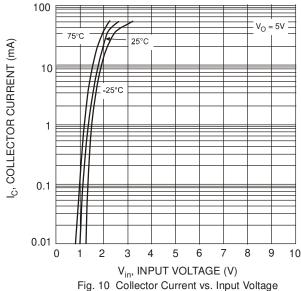




Typical Curves - DCX143EH PNP Section



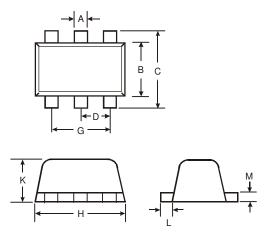






Package Outline Dimensions

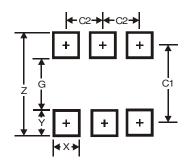
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT563							
Dim	Min	Max	Тур					
Α	0.15	0.30	0.20					
В	1.10	1.25	1.20					
С	1.55	1.70	1.60					
D	-	-	0.50					
G	0.90	1.10	1.00					
Н	1.50	1.70	1.60					
K	0.55	0.60	0.60					
L	0.10	0.30	0.20					
М	0.10	0.18	0.11					
All	Dimens	sions in	mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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